

S14644 series

High speed, compact Si APD for LiDAR (800 nm band) featuring low-bias operation

The S14644 series is a compact, surface mount type Si APD that achieves high sensitivity in the 800 nm band. This is suitable for laser monitoring of optical rangefinders widely used from consumer electronics to industrial use.

Features

- **Small package: 3.1 × 1.8 × 1.0^t mm**
- **Peak sensitivity wavelength: 800 nm (M=100)**
- **Low-bias operation: Breakdown voltage=180 V max.**
- **High-speed response: Cutoff frequency=1 GHz typ. (λ=800 nm, M=100)**
- **Reduction of breakdown voltage variation 160 ± 20 V**

Applications

- **Optical rangefinders**

Structure

Parameter	S14644-02	S14644-05	Unit
Photosensitive area*1	φ0.2	φ0.5	mm
Effective photosensitive area	0.03	0.19	mm ²
Package	Glass epoxy (silicone resin)		-

*1: Photosensitive area in which a typical gain can be obtained

Absolute maximum ratings

Parameter	Symbol	Specification	Unit
Reverse current (DC)	I _R max	0.2	mA
Forward current	I _F max	10	mA
Operating temperature*2	T _{opr}	-30 to +100	°C
Storage temperature*2	T _{stg}	-40 to +100	°C
Soldering temperature	T _{sol}	260 (3 times)*3	°C

*2: No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environments, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

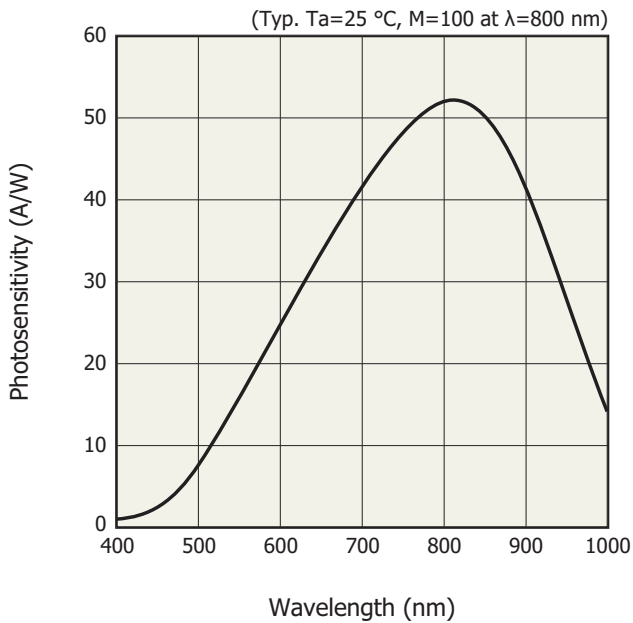
*3: Reflow soldering, JEDEC J-STD-020 MSL 2a, see P.5

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

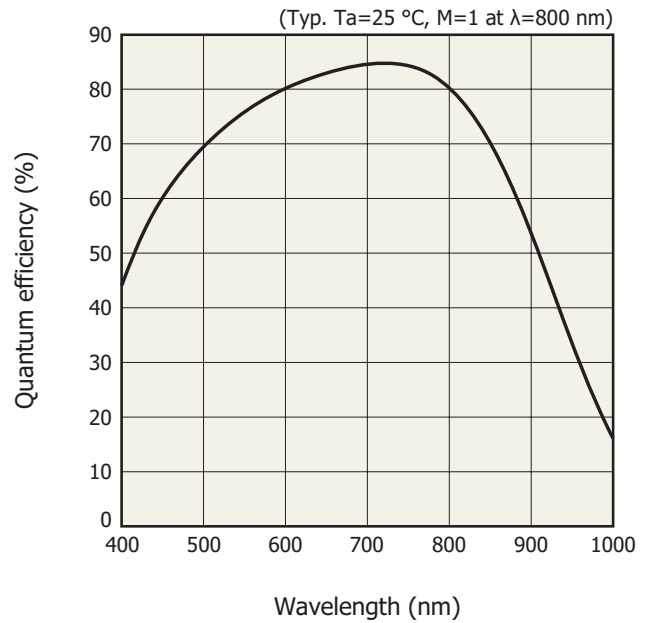
Electrical and optical characteristics (Ta=25 °C)

Parameter	Symbol	Condition	S14644-02			S14644-05			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Spectral response range	λ		400 to 1000						nm
Peak sensitivity wavelength	λ_p		-	800	-	-	800	-	nm
Photosensitivity	S	$\lambda=800$ nm, M=1	-	0.52	-	-	0.52	-	A/W
Quantum efficiency	QE	$\lambda=800$ nm, M=1	-	80	-	-	80	-	%
Breakdown voltage	V _{BR}	I _D =100 μ A	140	160	180	140	160	180	V
Temperature coefficient of breakdown voltage	$\Delta T_{V_{BR}}$		-	0.63	-	-	0.63	-	V/°C
Dark current	I _D	M=100	-	30	300	-	50	500	pA
Temperature coefficient of dark current	ΔT_{I_D}	M=100	-	1.1	-	-	1.1	-	times/°C
Cutoff frequency	f _c	M=100, R _L =50 Ω $\lambda=800$ nm, -3 dB	-	1.2	-	-	1	-	GHz
Terminal capacitance	C _t	M=100, f=1 MHz	-	0.6	-	-	1.6	-	pF
Excess noise figure	x	M=100, $\lambda=800$ nm	-	0.3	-	-	0.3	-	-
Gain	M	$\lambda=800$ nm	-	100	-	-	100	-	-

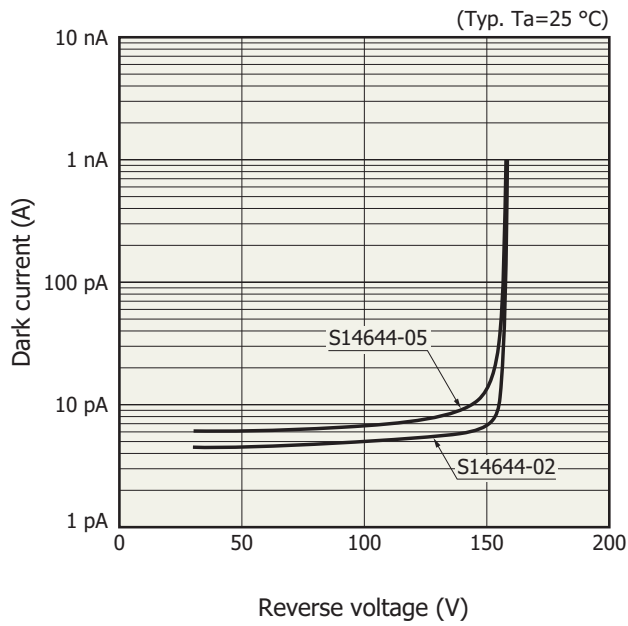
Spectral response



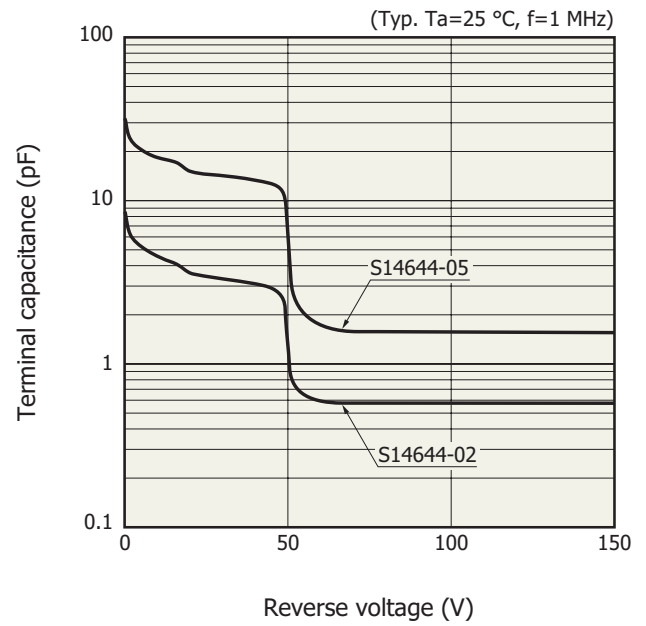
Quantum efficiency vs. wavelength



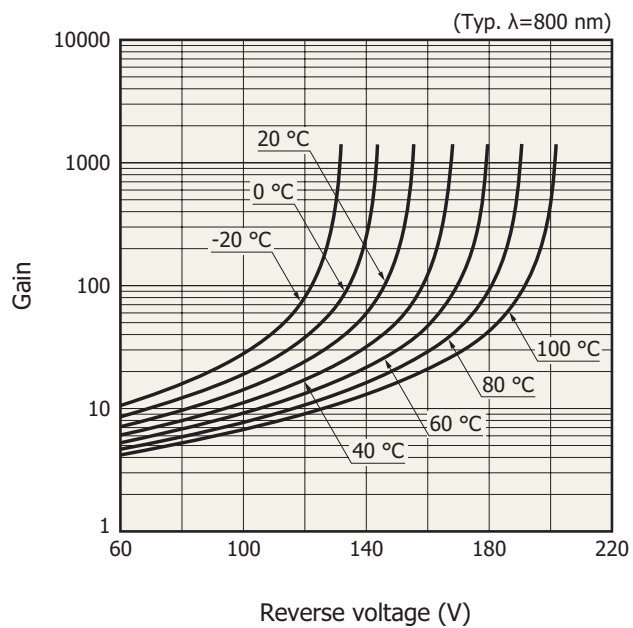
Dark current vs. reverse voltage



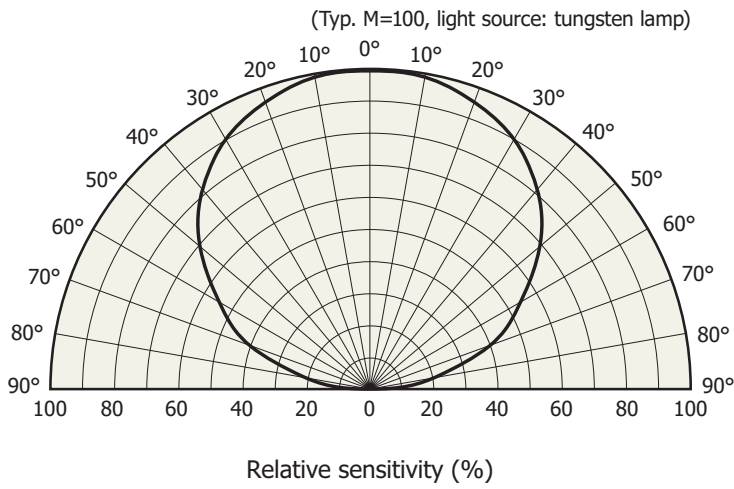
Terminal capacitance vs. reverse voltage



Gain vs. reverse voltage

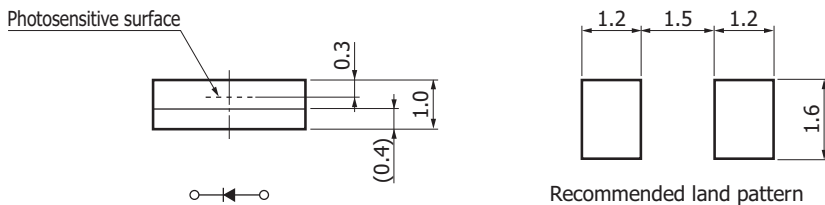
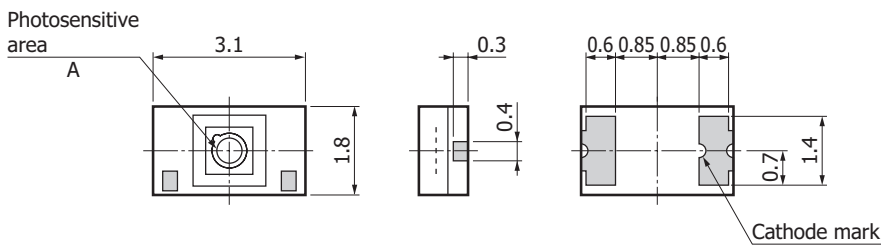


Directivity



KAPDB0450EA

Dimensional outline (unit: mm)



Tolerance unless otherwise noted: ± 0.2

Photosensitive area position accuracy:
X, Y $\leq \pm 0.2$

Type no.	A
S14644-02	$\phi 0.2$
S14644-05	$\phi 0.5$

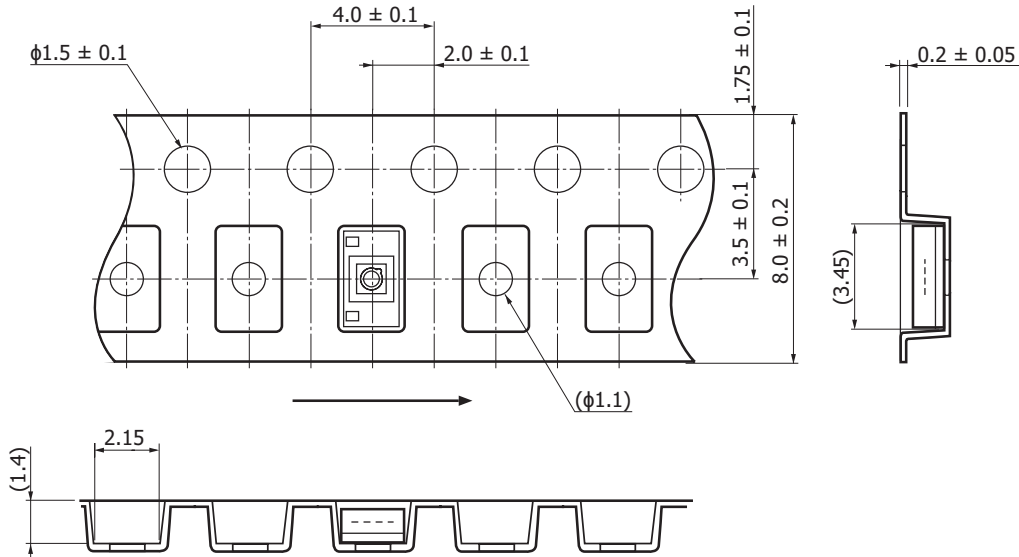
KAPDA0204EA

Standard packing specifications

- Reel (conforms to JEITA ET-7200)

Outer diameter	Hub diameter	Tape width	Material	Electrostatic characteristics
φ180 mm	φ60 mm	8 mm	PS	Conductive

- Embossed tape (unit: mm, material: PS, conductive)



KPINC0023EB

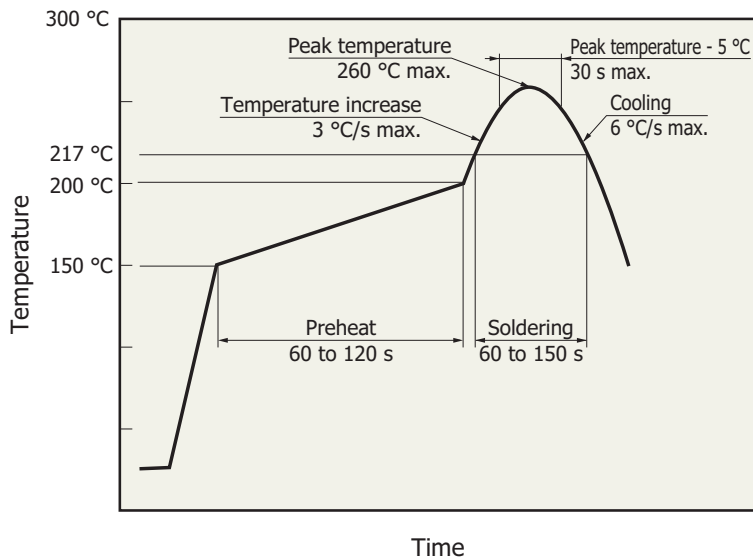
- Packing quantity

1000 pcs/reel

- Packing type

Reel and desiccant in moisture-proof packaging (vacuum-sealed)

Recommended reflow soldering conditions



KMPDB0405EC

- After unpacking, store the device in an environment at a temperature of 30 °C or less and a humidity of 60% or less, and perform reflow soldering within 4 weeks.
- The effect that the product receives during reflow soldering varies depending on the circuit board and the reflow oven that are used. When you set reflow soldering conditions, check that problems do not occur in the product by testing out the conditions in advance.

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions

- Disclaimer
- Surface mount type products

■ Technical information

- Si photodiodes / Technical note

Information described in this material is current as of March 2021.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

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HAMAMATSU

www.hamamatsu.com

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81)53-434-3311, Fax: (81)53-434-5184

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, Bridgewater, N.J. 08807, U.S.A., Telephone: (1)908-231-0960, Fax: (1)908-231-1218, E-mail: usa@hamamatsu.com

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49)8152-375-0, Fax: (49)8152-265-8, E-mail: info@hamamatsu.de

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: (33)1 69 53 71 00, Fax: (33)1 69 53 71 10, E-mail: infos@hamamatsu.fr

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, UK, Telephone: (44)1707-294888, Fax: (44)1707-325777, E-mail: info@hamamatsu.co.uk

North Europe: Hamamatsu Photonics Norden AB: Torshamnsgatan 35 16440 Kista, Sweden, Telephone: (46)8-509 031 00, Fax: (46)8-509 031 01, E-mail: info@hamamatsu.se

Italy: Hamamatsu Photonics Italia S.r.l.: Strada della Moia, 1 int. 6, 20020 Arese (Milano), Italy, Telephone: (39)02-93 58 17 33, Fax: (39)02-93 58 17 41, E-mail: info@hamamatsu.it

China: Hamamatsu Photonics (China) Co., Ltd.: 1201 Tower B, Jiaming Center, 27 Dongsanhuan Beilu, Chaoyang District, 100020 Beijing, P.R.China, Telephone: (86)10-6586-6006, Fax: (86)10-6586-2866, E-mail: hpc@hamamatsu.com.cn

Taiwan: Hamamatsu Photonics Taiwan Co., Ltd.: 8F-3, No. 158, Section2, Gongdao 5th Road, East District, Hsinchu, 300, Taiwan R.O.C. Telephone: (886)3-659-0080, Fax: (886)3-659-0081, E-mail: info@hamamatsu.com.tw